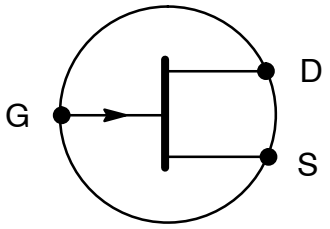
ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089
http://www.nteinc.com

NTE469
Silicon N–Channel JFET Transistor
Chopper, High Speed Switch
TO92 Type Package



Applications:
- Analog Switches
- Choppers
- Commutators

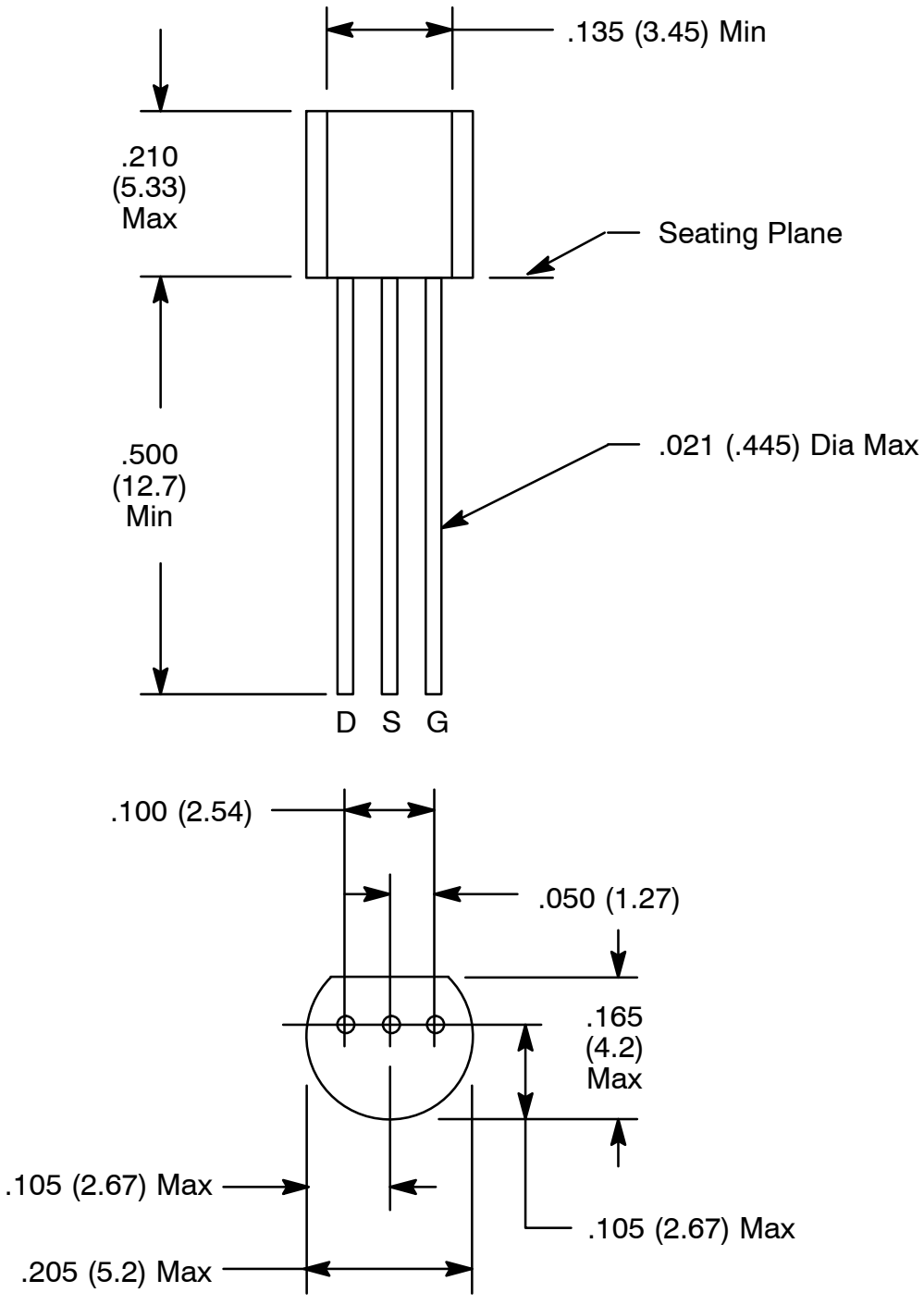
Absolute Maximum Ratings:

Drain–Source Voltage, V_{DS} 35V
Drain–Gate Voltage, V_{DG} 35V
Gate Current, I_G 50mA
Total Device Dissipation (T_A = +25°C), P_D 625mW
Derate Above 25°C . . . . . 5.68mW/°C
Operating Junction Temperature Range, T_J . . . . . –55° to +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C
Lead Temperature (During Soldering), T_L . . . . . +300°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Gate–Source Breakdown Voltage	$V_{(BR)GSS}$	I_G = 1 A, V_{DS} = 0	35	–	–	V
Gate Reverse Current	I_{GSS}	V_{GS} = –15V, V_{DS} = 0	–	–	–1.0	nA
Gate–Source Cutoff Voltage	$V_{GS(off)}$	V_{DS} = 5V, I_D = 1 A	–0.5	–	–3.0	V
Drain Cutoff Current	$I_{D(off)}$	V_{DS} = 5V, V_{GS} = –10V	–	–	1.0	nA
ON Characteristics						
Zero–Gate Voltage Drain Current	I_{DSS}	V_{DS} = 15V, V_{GS} = 0, Note 1	2.0	–	–	mA
Static Drain–Source ON Resistance	r_{DS}(on)	V_{DS} = 0.1V	–	–	100	°
Drain–Gate ON Capacitance	$C_{dg(on)}$	V_{DS} = V_{GS} = 0, f = 1MHz	–	–	28	pF
Source–Gate ON Capacitance	$C_{sg(on)}$	V_{DS} = V_{GS} = 0, f = 1MHz	–	–	28	pF
Drain–Gate OFF Capacitance	$C_{dg(off)}$	V_{GS} = –10V, f = 1MHz	–	–	5	pF
Source–Gate OFF Capacitance	$C_{sg(off)}$	V_{GS} = –10V, f = 1MHz	–	–	5	pF

Note 1. Pulse Test: Pulse Width = 300 s, Duty Cycle = 3%.


.135 (3.45) Min
.210
(5.33)
Max
Seating Plane
.500
(12.7)
Min
.021 (.445) Dia Max
D S G
.100 (2.54)
.050 (1.27)
.165
(4.2)
Max
.105 (2.67) Max
.105 (2.67) Max
.205 (5.2) Max